

Publication

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Application

EP 93109418 A 19930611

Priority

JP 17942992 A 19920612

Abstract (en)

[origin: EP0577998A2] It has a purpose to provide a field effect transistor so as to realize high intensive function in a LSI. A field effect transistor of this invention comprises a plural number of gates, to each of which an independent current is connected, and an output is generated by totalizing of characteristics "gate voltage vs. drain current" of the gates. <IMAGE>

IPC 1-7

H01L 29/76; **H01L 29/60**

IPC 8 full level

H01L 29/78 (2006.01)

CPC (source: EP KR)

H01L 29/78 (2013.01 - KR); **H01L 29/7831** (2013.01 - EP)

Citation (search report)

- [X] US 5005059 A 19910402 - GOLIO JOHN M [US], et al
- [A] US 3355598 A 19671128 - TUSKA JAMES W
- [X] PATENT ABSTRACTS OF JAPAN vol. 6, no. 128 (E - 118)<1006> 14 July 1982 (1982-07-14)
- [X] PATENT ABSTRACTS OF JAPAN vol. 011, no. 7 (E - 469) 9 January 1987 (1987-01-09)
- [X] M. G. SMITH: "DEVICE TAILORING PROCEDURE", IBM TECHNICAL DISCLOSURE BULLETIN, vol. 7, no. 11, April 1965 (1965-04-01), NEW YORK US, pages 1100

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